## **CLAIMS**

What is claimed is:

1	1. A thermoelectric apparatus, comprising:
2	a first electrode;
3	a dielectric material proximate said first electrode;
4	a second electrode opposing said first electrode with said dielectric material
5	deposed therebetween; and
6	at least one nano-wire extending between said first electrode and said second
7	electrode.
1	2. The apparatus of claim 1, wherein said at least one nano-wire comprises a
2	bismuth containing material.
1	3. The apparatus of claim 1, wherein said dielectric material comprises a
2	porous dielectric material.
1	4. The apparatus of claim 3, wherein said porous dielectric material
2	comprises porous alumina.
1	5. The apparatus of claim 1, further comprising a negatively charged trace
2	electrically connected to said first electrode and a positively charged trace to said second
3	electrode.

- 1 6. A thermoelectric package, comprising: 2 a microelectronic die having at least one area of which is of a higher heat dissipation rate than the remainder of the microelectronic die when in operation; 3 4 a first electrode proximate said microelectronic die including said higher heat 5 area; 6 a dielectric material proximate said first electrode; 7 a second electrode opposing said first electrode with said dielectric material 8 disposed therebetween; and 9 a plurality of nano-wires extending between said first electrode and said second 10 electrode.
- 7. The package of claim 6, wherein said nano-wires are dispersed in a higher density proximate said at least one higher heat dissipation rate area.
- 1 8. The package of claim 6, wherein said at least one nano-wire comprises a 2 bismuth containing material.
- 1 9. The package of claim 6, wherein said dielectric material comprises a porous dielectric material.

2 porous alumina. The package of claim 6, further comprising a negatively charged trace 1 11. electrically connected to said first electrode and a positively charged trace to said second 2 3 electrode. 1 12. A method comprising: 2 providing a first electrode; disposing a dielectric material proximate said first electrode; 3 4 forming at least one nano-scale opening through the dielectric material; 5 disposing a conductive material within said at least one nano-scale opening to form at least one nano-wire which contacts said first electrode; and 6 7 forming a second electrode opposing said first electrode with said dielectric material deposed therebetween, wherein said second electrode contacts said at least one 8 9 nano-wire. The method of claim 12, wherein disposing said conductive material 1 13. 2 comprising disposing a bismuth containing material. The method of claim 12, wherein disposing said dielectric material 1 14. 2 comprises disposing a porous dielectric material.

The package of claim 9, wherein said porous dielectric material comprises

1

10.

1 15. The method of claim 14, wherein disposing said porous dielectric material 2 comprises disposing porous alumina. 1 16. The method of claim 12, further comprising forming a negatively charged 2 trace electrically connected to said first electrode and forming a positively charged trace 3 to said second electrode. 1 17. A method comprising: 2 providing a first electrode; 3 disposing a porous dielectric material proximate said first electrode; 4 disposing a conductive material on said porous dielectric material, wherein said 5 conductive material extends through at least one opening in said porous material to form 6 at least one nano-wire which contacts said first electrode; and 7 forming a second electrode opposing said first electrode with said dielectric 8 material deposed therebetween, wherein said second electrode contacts said at least one 9 nano-wire. 18. 1 The method of claim 17, wherein disposing said conductive material on

Ref. No.: 42P19016

porous dielectric material.

2

3

said porous dielectric material comprises disposing a bismuth containing material on said

- 1 19. The method of claim 19, wherein disposing said porous dielectric material comprises disposing porous alumina.
- 1 20. The method of claim 17, further comprising forming a negatively charged 2 trace electrically connected to said first electrode and forming a positively charged trace 3 to said second electrode.
- 1 21. An electronic system, comprising:
- an external substrate within a housing; and
- at least one microelectronic device package attached to said external substrate,
- 4 having at least thermoelectric device including:
- 5 a first electrode;
- a dielectric material proximate said first electrode;
- 7 a second electrode opposing said first electrode with said dielectric
- 8 material deposed therebetween; and
- 9 at least one nano-wire extending between said first electrode and said
- second electrode;
- an input device interfaced with said external substrate; and
- 12 a display device interfaced with said external substrate.
- 1 22. The system of claim 21, wherein said at least one nano-wire comprises a bismuth containing material.

- 1 23. The system of claim 21, wherein said dielectric material comprises a
- 2 porous dielectric material.
- 1 24. The system of claim 23, wherein said porous dielectric material comprises
- 2 porous alumina.
- 1 25. The system of claim 21, wherein said thermoelectric device further
- 2 comprises a negatively charged trace electrically connected to said first electrode and a
- 3 positively charged trace to said second electrode.